

NTST30U100CT, NTSB30U100CT-1, NTSJ30U100CTG, NTSB30U100CTG

Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low $V_F = 0.42\text{ V}$ at $I_F = 5\text{ A}$

Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- Pb-Free and Halide-Free Packages are Available

Typical Applications

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec

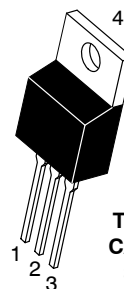
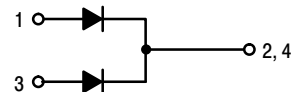


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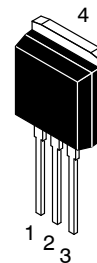
www.onsemi.com

VERY LOW FORWARD VOLT-
AGE, LOW LEAKAGE SCHOT-
TKY BARRIER
RECTIFIERS 30 AMPERES,
100 VOLTS

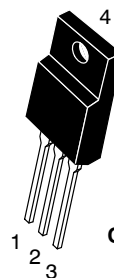
PIN CONNECTIONS



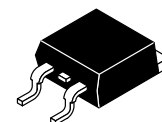
TO-220AB
CASE 221A
STYLE 6



I2PAK
CASE 418D
STYLE 3



TO-220FP
CASE 221AH



D2PAK
CASE 418B

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

NTST30U100CT, NTSB30U100CT-1, NTSJ30U100CTG, NTSB30U100CTG

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	100	V
Average Rectified Forward Current (Rated V_R , $T_C = 125^\circ\text{C}$)	$I_{F(AV)}$ Per device Per diode	30 15	A
Peak Repetitive Forward Current (Rated V_R , Square Wave, 20 kHz, $T_C = 120^\circ\text{C}$)	I_{FRM} Per device Per diode	60 30	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	160	A
Operating Junction Temperature	T_J	-40 to +150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to +150	$^\circ\text{C}$
Voltage Rate of Change (Rated V_R)	dv/dt	10,000	V/ μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Rating	Symbol	NTST30U100CTG, NTSB30U100CT-1G	NTSB30U100CTG	NTSJ30U100CTG	Unit
Maximum Thermal Resistance per Diode Junction-to-Case Junction-to-Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.5 70	0.93 46.5	3.81 105	$^\circ\text{C}/\text{W}$ $^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

Rating	Symbol	Typ	Max	Unit
Maximum Instantaneous Forward Voltage (Note 1) ($I_F = 5\text{ A}$, $T_J = 25^\circ\text{C}$) ($I_F = 7.5\text{ A}$, $T_J = 25^\circ\text{C}$) ($I_F = 15\text{ A}$, $T_J = 25^\circ\text{C}$) ($I_F = 5\text{ A}$, $T_J = 125^\circ\text{C}$) ($I_F = 7.5\text{ A}$, $T_J = 125^\circ\text{C}$) ($I_F = 15\text{ A}$, $T_J = 125^\circ\text{C}$)	V_F	0.47 0.52 0.66 0.42 0.48 0.60	– – 0.80 – – 0.65	V
Maximum Instantaneous Reverse Current (Note 1) ($V_R = 70\text{ V}$, $T_J = 25^\circ\text{C}$) ($V_R = 70\text{ V}$, $T_J = 125^\circ\text{C}$) (Rated dc Voltage, $T_J = 25^\circ\text{C}$) (Rated dc Voltage, $T_J = 125^\circ\text{C}$)	I_R	15 12 65 32	 675 60	μA mA μA mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$

TYPICAL CHARACTERISTICS

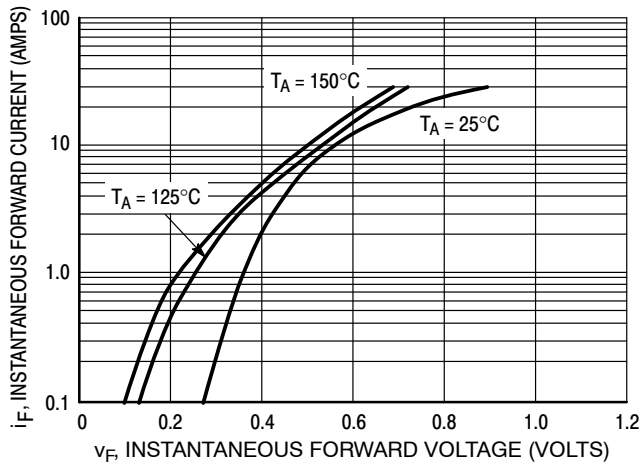


Figure 1. Typical Forward Voltage

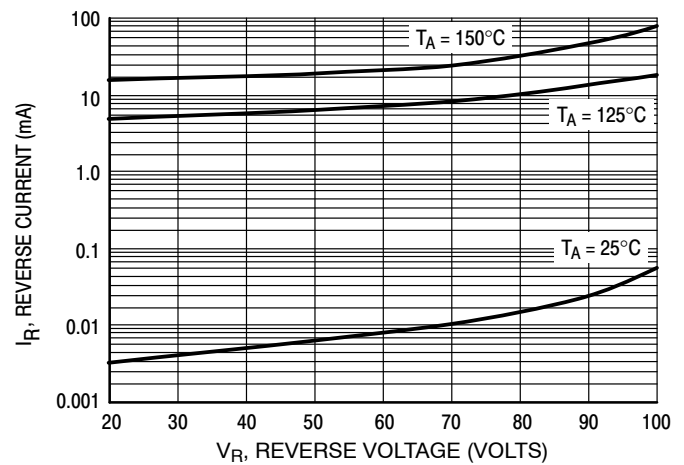


Figure 2. Typical Reverse Current

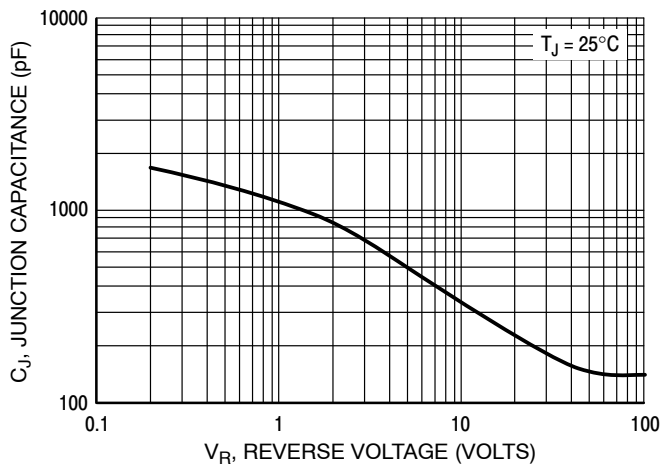


Figure 3. Typical Junction Capacitance

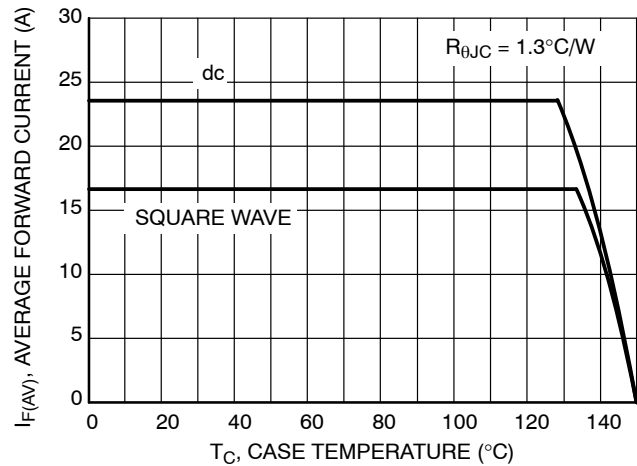


Figure 4. Current Derating per Leg

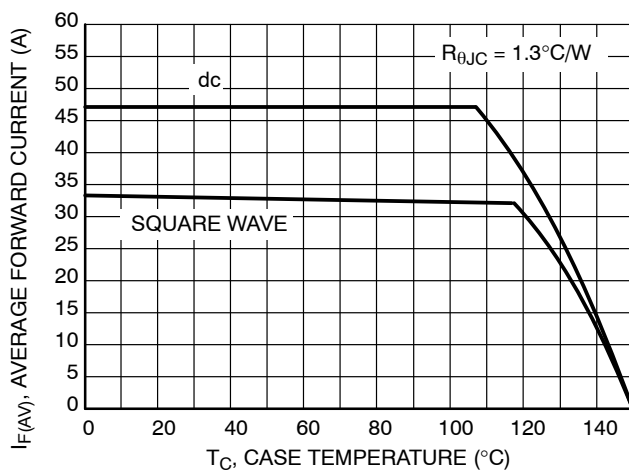


Figure 5. Current Derating, Case

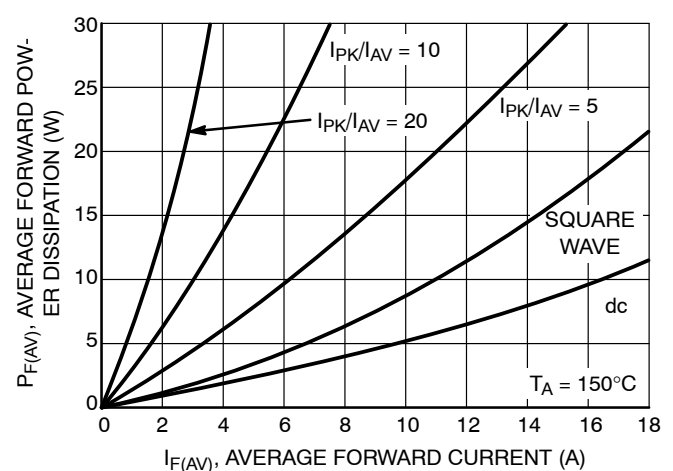


Figure 6. Forward Power Dissipation

TYPICAL CHARACTERISTICS

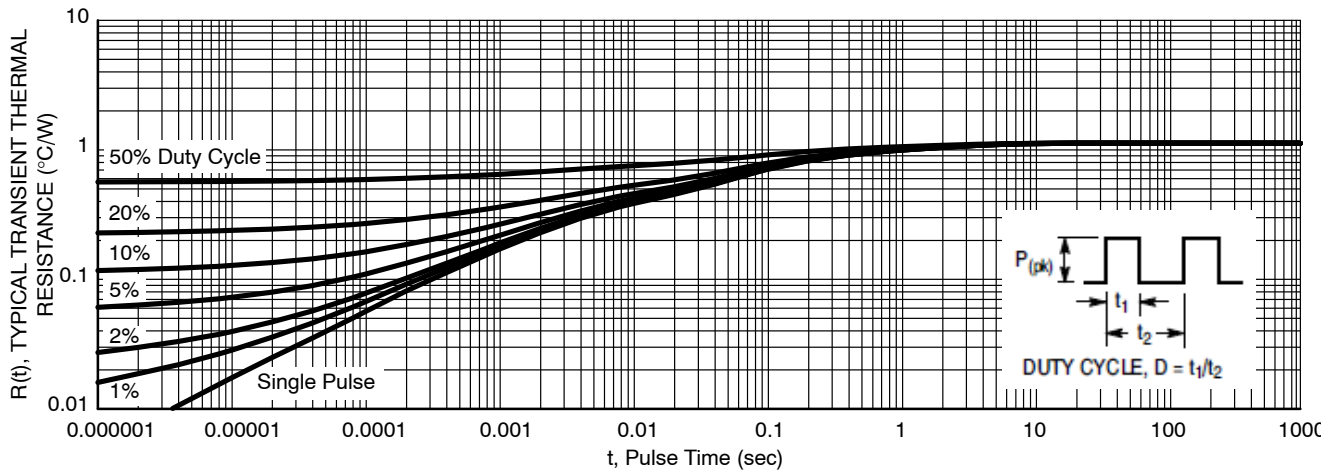


Figure 7. Typical Transient Thermal Response, Junction-to-Case for NTST30U100CT and NTSB30U100CT-1G

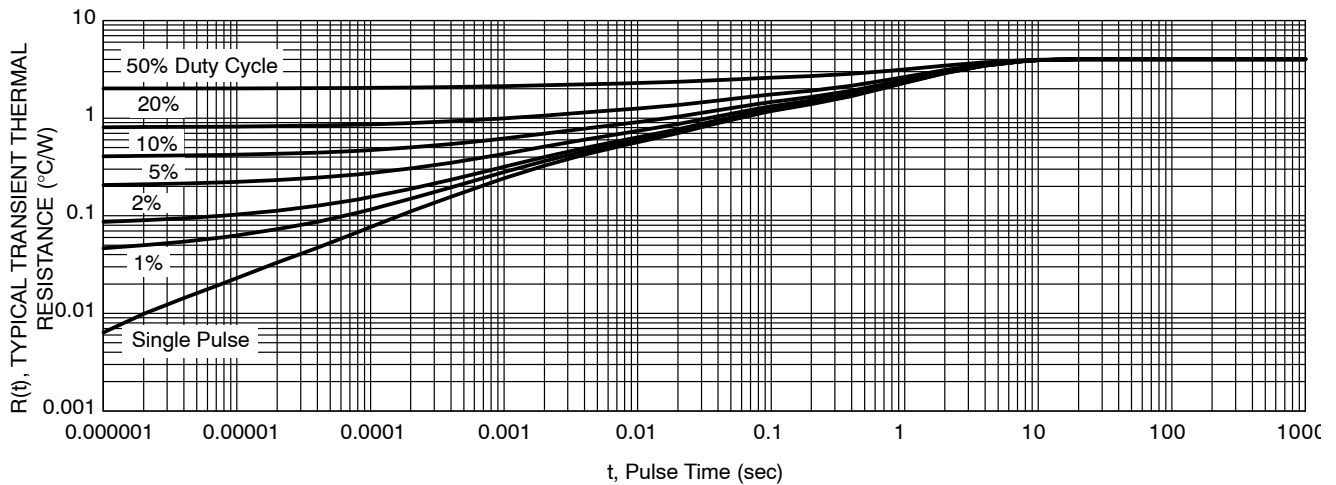


Figure 8. Typical Transient Thermal Response, Junction-to-Case for NTSJ30U100CTG

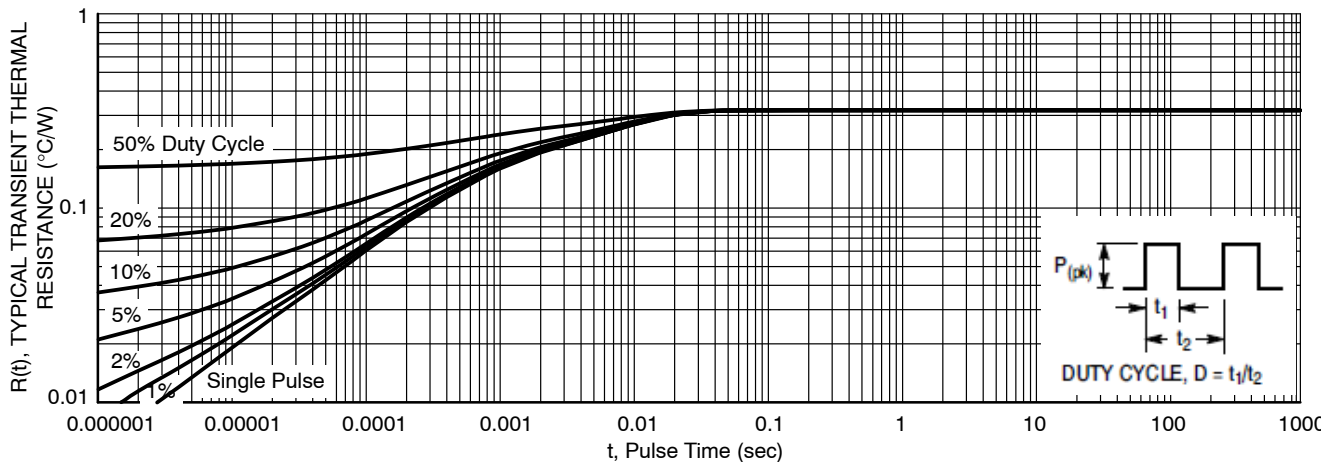


Figure 9. Typical Transient Thermal Response, Junction-to-Case for NTSB30U100CTG

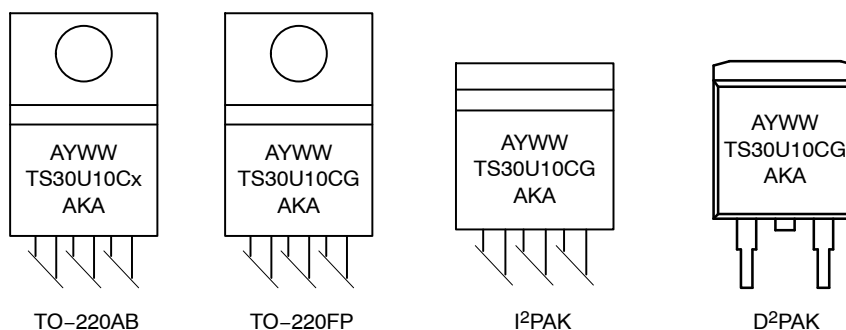
NTST30U100CT, NTSB30U100CT-1, NTSJ30U100CTG, NTSB30U100CTG

ORDERING INFORMATION

Device	Package	Shipping†
NTST30U100CTG	TO-220AB (Pb-Free)	50 Units / Rail
NTST30U100CTH	TO-220AB (Halide-Free)	50 Units / Rail
NTSB30U100CT-1G	I ² PAK (Pb-Free)	50 Units / Rail
NTSJ30U100CTG	TO-220FP (Halide-Free)	50 Units / Rail
NTSB30U100CTG	D ² PAK (Pb-Free)	50 Units / Rail
NTSB30U100CTT4G	D ² PAK (Pb-Free)	800 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

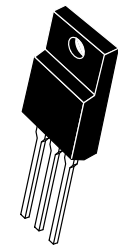
MARKING DIAGRAMS



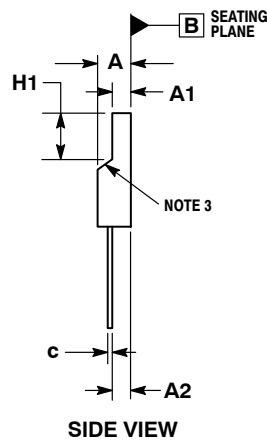
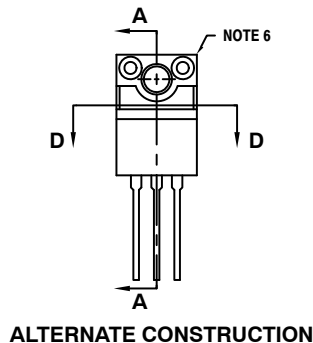
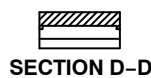
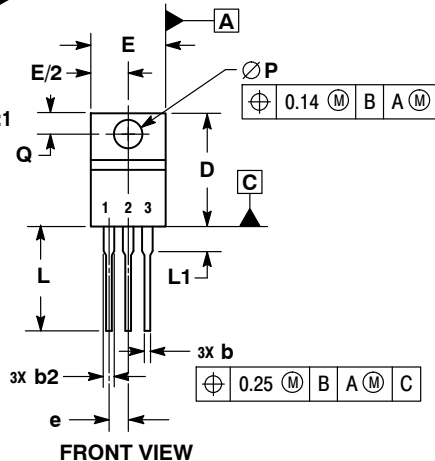
A = Assembly Location
 Y = Year
 WW = Work Week
 AKA = Polarity Designator
 x = G or H
 G = Pb-Free Package
 H = Halide-Free Package

TO-220 FULLPACK, 3-LEAD CASE 221AH ISSUE F

DATE 30 SEP 2014



SCALE 1:1

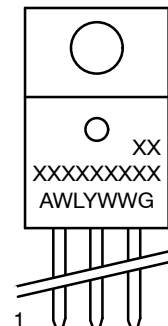


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR UNCONTROLLED IN THIS AREA.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.
6. CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY MAY VARY WITHIN THE ENVELOPE DEFINED BY DIMENSIONS A1 AND H1 FOR MANUFACTURING PURPOSES.

DIM	MIN	MAX
A	4.30	4.70
A1	2.50	2.90
A2	2.50	2.90
b	0.54	0.84
b2	1.10	1.40
c	0.49	0.79
D	14.70	15.30
E	9.70	10.30
e	2.54 BSC	
H1	6.60	7.10
L	12.50	14.73
L1	---	2.80
P	3.00	3.40
Q	2.80	3.20

GENERIC MARKING DIAGRAM*



A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package

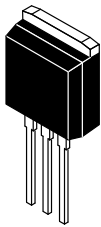
*This information is generic. Please refer to device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE

STYLE 2:
PIN 1. CATHODE
2. ANODE
3. GATE

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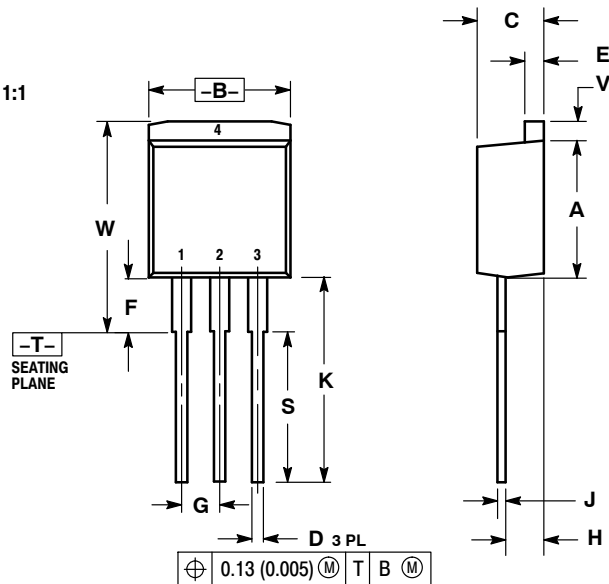
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SCALE 1:1

I²PAK (TO-262)
CASE 418D-01
ISSUE D

DATE 16 OCT 2007



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.335	0.380	8.51	9.65
B	0.380	0.406	9.65	10.31
C	0.160	0.185	4.06	4.70
D	0.026	0.035	0.66	0.89
E	0.045	0.055	1.14	1.40
F	0.122 REF		3.10 REF	
G	0.100 BSC		2.54 BSC	
H	0.094	0.110	2.39	2.79
J	0.013	0.025	0.33	0.64
K	0.500	0.562	12.70	14.27
S	0.390 REF		9.90 REF	
V	0.045	0.070	1.14	1.78
W	0.525	0.551	13.25	14.00

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

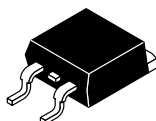
STYLE 4:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

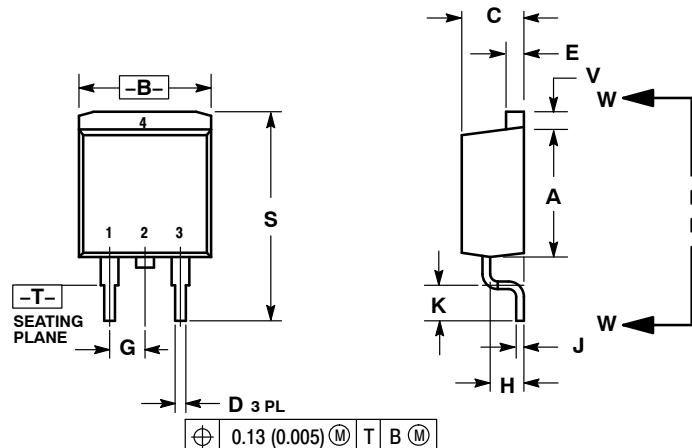
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D²PAK 3
CASE 418B-04
ISSUE L

DATE 17 FEB 2015

SCALE 1:1

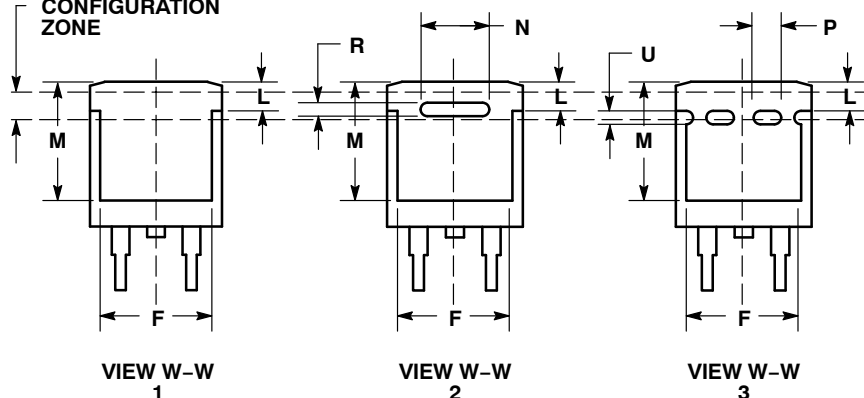


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100	BSC	2.54	BSC
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197	REF	5.00	REF
P	0.079	REF	2.00	REF
R	0.039	REF	0.99	REF
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

VARIABLE CONFIGURATION ZONE



STYLE 1:

- PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:

- PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:

- PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 4:

- PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 5:

- PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:

- PIN 1. NO CONNECT
2. CATHODE
3. ANODE
4. CATHODE

MARKING INFORMATION AND FOOTPRINT ON PAGE 2

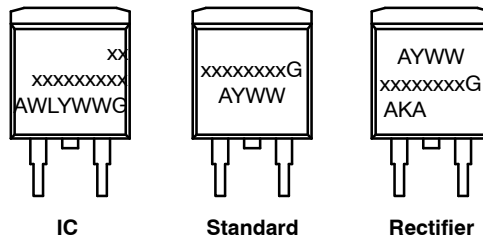
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D²PAK 3
CASE 418B-04
ISSUE L

DATE 17 FEB 2015

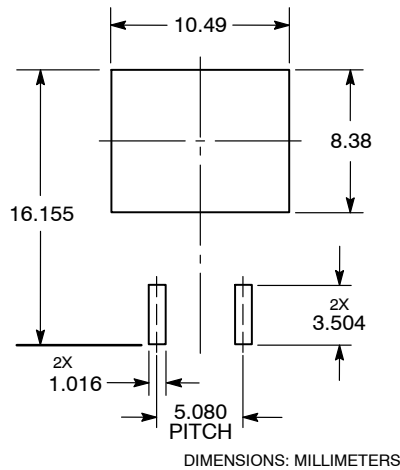
**GENERIC
MARKING DIAGRAM***



xx = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package
AKA = Polarity Indicator

*This information is generic. Please refer to device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot "▪", may or may not be present.

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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